

General Description

These N-Channel enhancement mode power field effect transistors are produced using advanced technology which has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficient switched mode power supplies and active power factor correction.

Features

- 100% avalanche tested
- Fast Switching
- Improved dv/dt capability

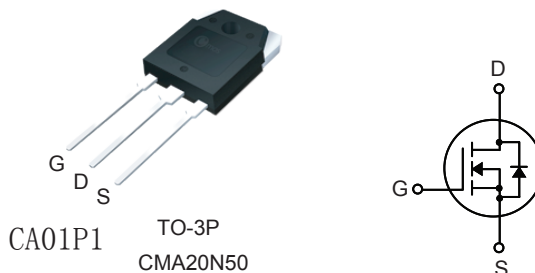
Product Summary

BVDSS	RDSON	ID
500V	0.26Ω	20A

Applications

- DC-DC converters
- Switching regulators
- UPS (Uninterruptible Power Supply)

TO-3P Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	500	V
V_{GS}	Gate-Source Voltage	±30	V
$I_D@T_C=25^{\circ}C$	Continuous Drain Current	20	A
$I_D@T_C=100^{\circ}C$	Continuous Drain Current	12	A
I_{DM}	Pulsed Drain Current ¹	60	A
EAS	Single Pulse Avalanche Energy ²	860	mJ
$P_D@T_C=25^{\circ}C$	Total Power Dissipation	280	W
T_{STG}	Storage Temperature Range	-55 to 150	°C
T_J	Operating Junction Temperature Range	-55 to 150	°C

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient	---	40	°C/W
$R_{\theta JC}$	Thermal Resistance Junction-case	---	0.44	°C/W

Electrical Characteristics ($T_J=25^{\circ}\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V$, $I_D=250\mu A$	500	---	---	V
$\Delta BV_{DSS}/\Delta T_J$	BVDSS Temperature Coefficient	Reference to 25°C , $I_D=250\mu A$	---	0.5	---	V/ $^{\circ}\text{C}$
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=10V$, $I_D=10A$	---	---	0.26	Ω
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}$, $I_D=250\mu A$	2	---	4	V
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=500V$, $V_{GS}=0V$	---	---	1	μA
		$V_{DS}=400V$, $V_{GS}=0V$, $T_C=125^{\circ}\text{C}$	---	---	10	
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 30V$, $V_{DS}=0V$	---	---	± 100	nA
g_{fs}	Forward Transconductance ³	$V_{DS}=40V$, $I_D=10A$	---	24	---	S
Q_g	Total Gate Charge	$I_D=20A$	---	52	69	nC
Q_{gs}	Gate-Source Charge	$V_{DS}=400V$	---	18	---	
Q_{gd}	Gate-Drain Charge	$V_{GS}=10V$ (Note 3, 4)	---	26	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DS}=250V$	---	88	---	ns
T_r	Rise Time	$I_D=20A$	---	270	---	
$T_{d(off)}$	Turn-Off Delay Time	$R_G=25\Omega$	---	105	---	
T_f	Fall Time	(Note 3, 4)	---	117	---	
C_{iss}	Input Capacitance	$V_{DS}=25V$, $V_{GS}=0V$, $f=1\text{MHz}$	---	4000	---	pF
C_{oss}	Output Capacitance		---	380	---	
C_{rss}	Reverse Transfer Capacitance		---	35	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current	$V_G=V_D=0V$, Force Current	---	---	20	A
I_{SM}	Pulsed Source Current		---	---	60	A
V_{SD}	Diode Forward Voltage	$V_{GS}=0V$, $I_S=20A$, $T_J=25^{\circ}\text{C}$	---	---	1.4	V

Note :

- 1.Repetitive Rating: Pulse width limited by maximum junction temperature
- 2.L = 4.1mH, $I_{AS} = 20A$, $V_{DD} = 50V$, $R_G = 25\Omega$, Starting $T_J = 25^{\circ}\text{C}$
- 3.Pulse Test: Pulse width $\leq 300\mu s$, Duty Cycle $\leq 2\%$
- 4.Essentially Independent of Operating Temperature Typical Characteristics

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